

# Ways to Fabricate Quantum Processor Chips

Onri Jay Benally

University of Minnesota

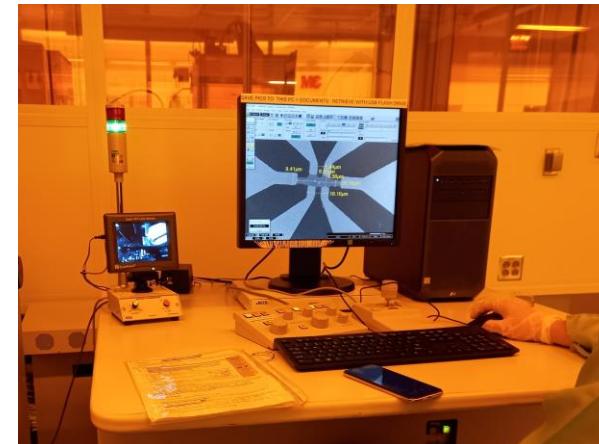
Department of Electrical & Computer Engineering

Principal Investigator: Prof. Jian-Ping Wang



# Table of Contents

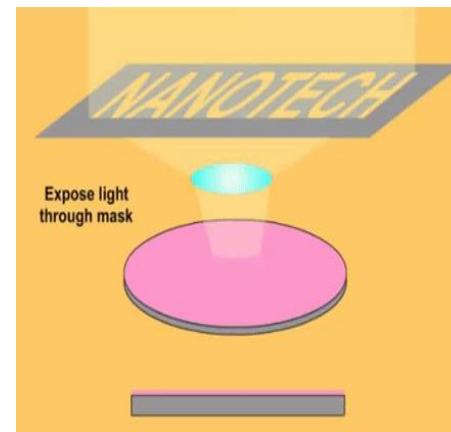
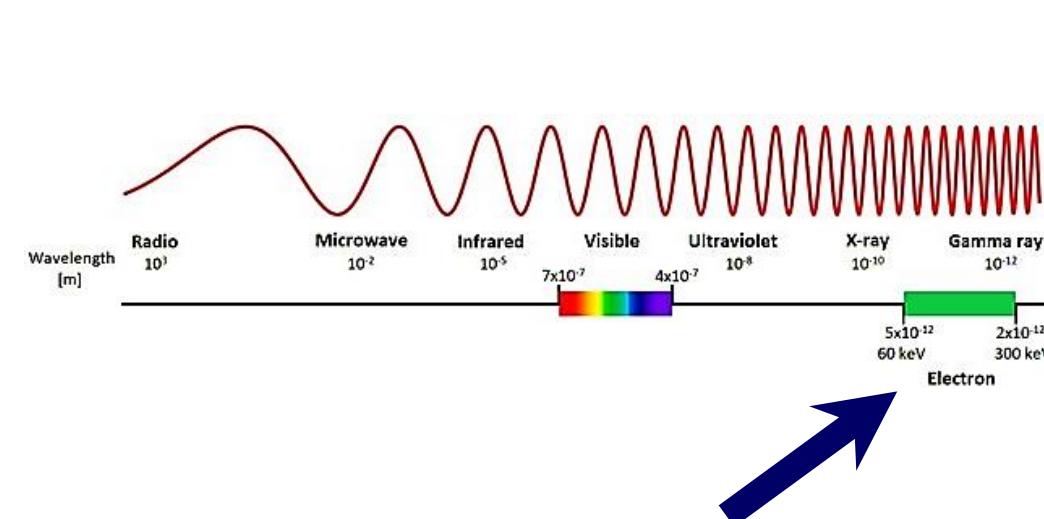
- I. Background & Motivation.
- II. Design Process Flow.
- III. Electron-Beam Lithography vs. 3D Printing vs. CNC Machining.
- IV. Maskless Direct Writing.
- V. Equipment Advantages & Disadvantages.
- VI. Example Chips.
- VII. Conclusion.



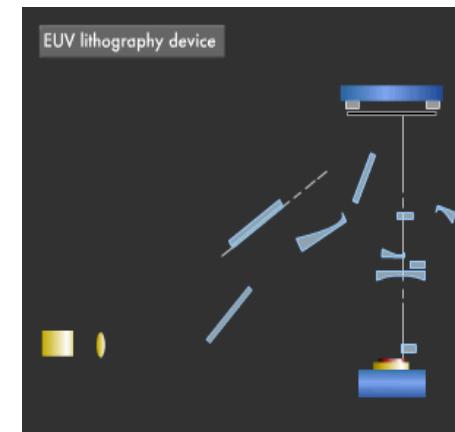
Scanning Electron Microscope from JEOL, *Onri Jay Benally* (2022)

# Background & Motivation

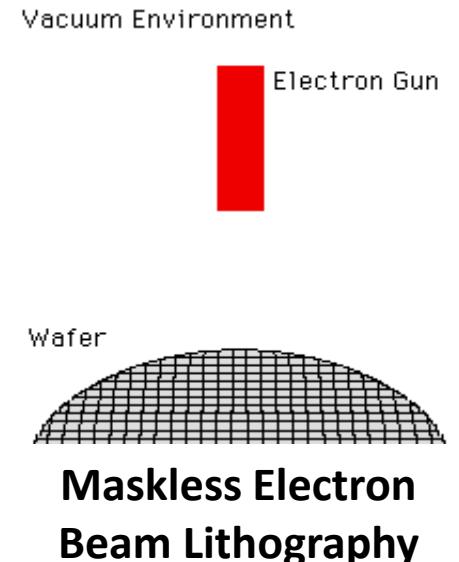
- Conventional optical lithography = **ultraviolet photon** exposure.
- Electron beam lithography = **electron** beam exposure.
- Ultimately, the *wavelength* of the energy being applied to a resist coating determines the feature size.
- It's possible to obtain 3-5 nm resolution with electron-beam lithography
  - Depends on your skill level (abstract).



Maskless Ultraviolet  
Lithography



Maskless Extreme  
Ultraviolet  
Lithography



Maskless Electron  
Beam Lithography

1. Venturi, *PhD Thesis* (2017)
2. Taken from: [thumbs.gfycat.com](http://thumbs.gfycat.com)
3. Taken from: [Wikimedia Commons](https://commons.wikimedia.org)



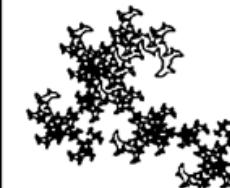
# Taxonomy of Plane-Filling Curves



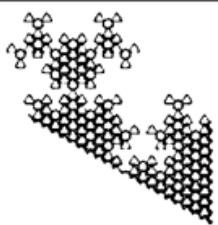
**G(1,1) norm 2 family**



**E(2,1) norm 3 family**



**G(2,0) norm 4 family**



**E(2,0) norm 4 family**



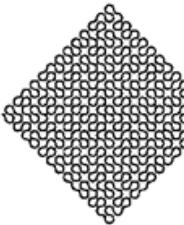
**G(2,1) norm 5 family**



**E(3,1) norm 7 family**



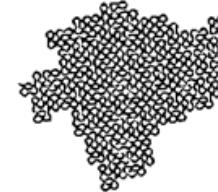
**G(2,2) norm 8 family**



**G(3,0) norm 9 family**



**E(3,0) norm 9 family**



**G(3,1) norm 10 family**

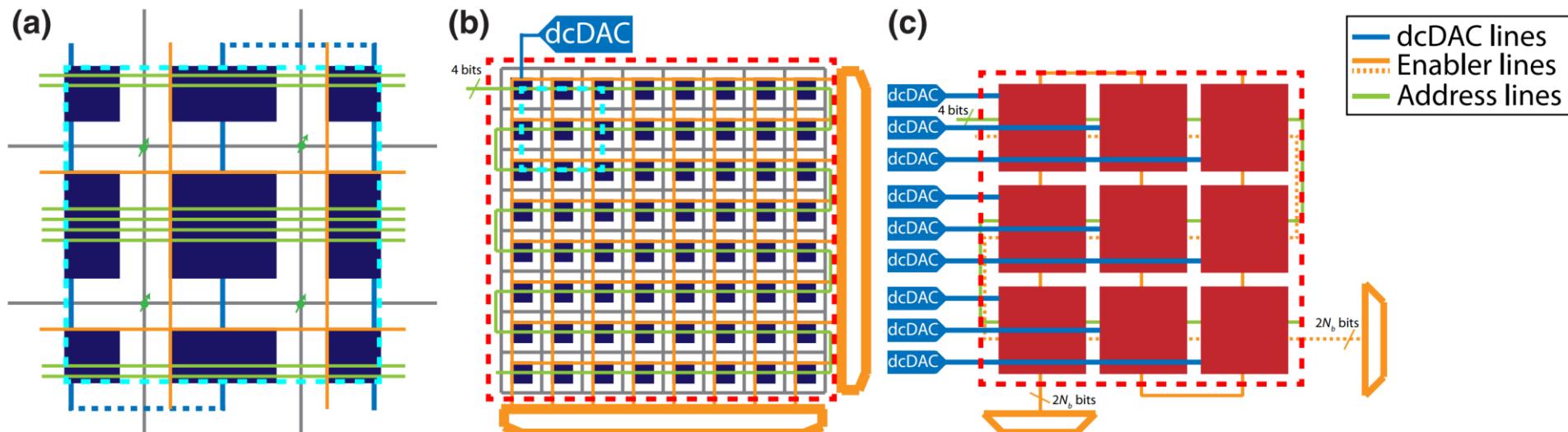
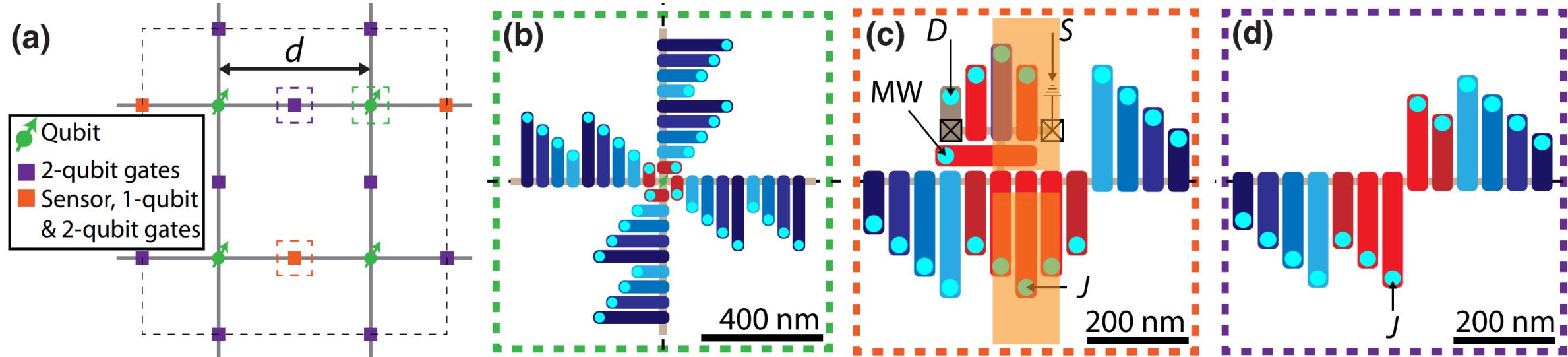


**E(3,4) norm 12 family**



**E(4,1) norm 13 family**

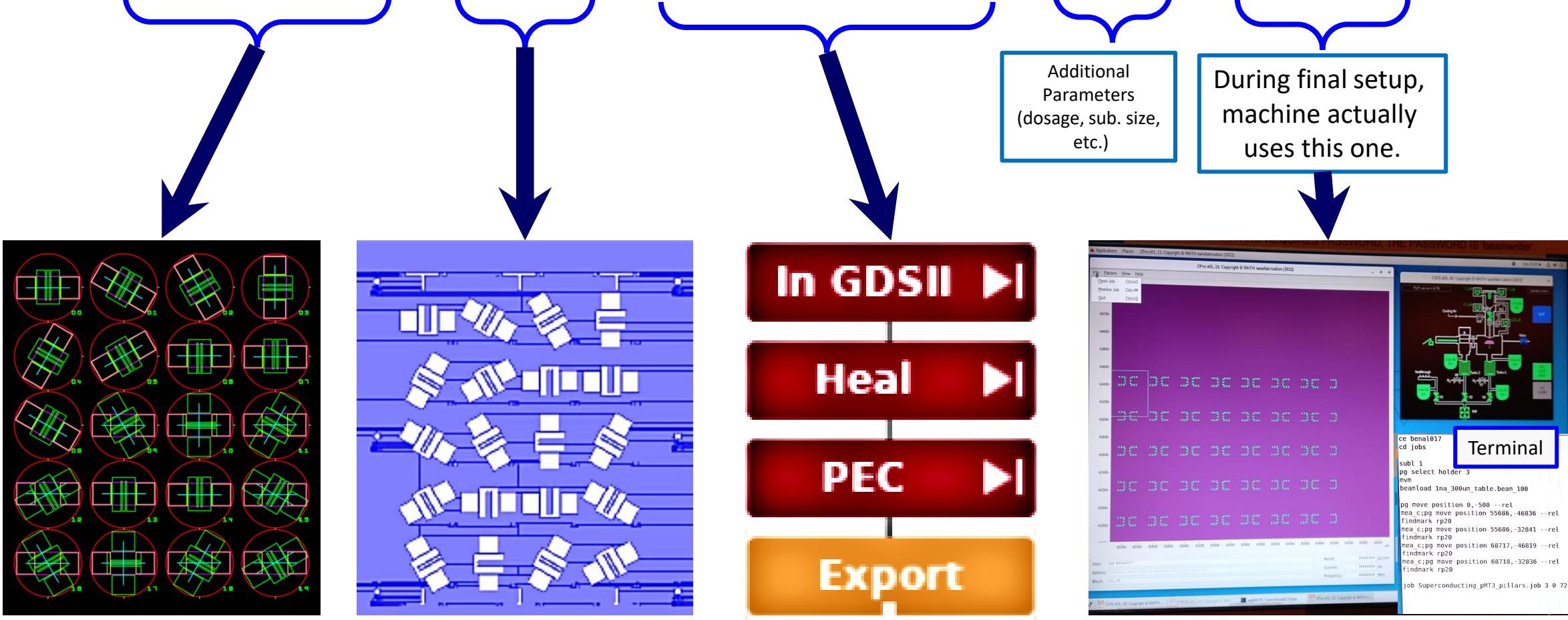
# Example of a Spin Qubit Array



# Design Process Flow

- Design file conversion is a bit extensive.

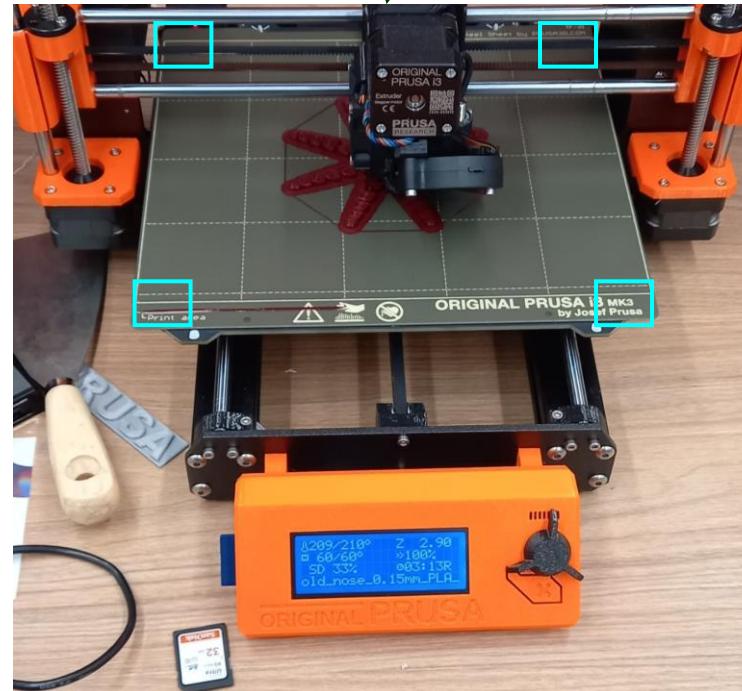
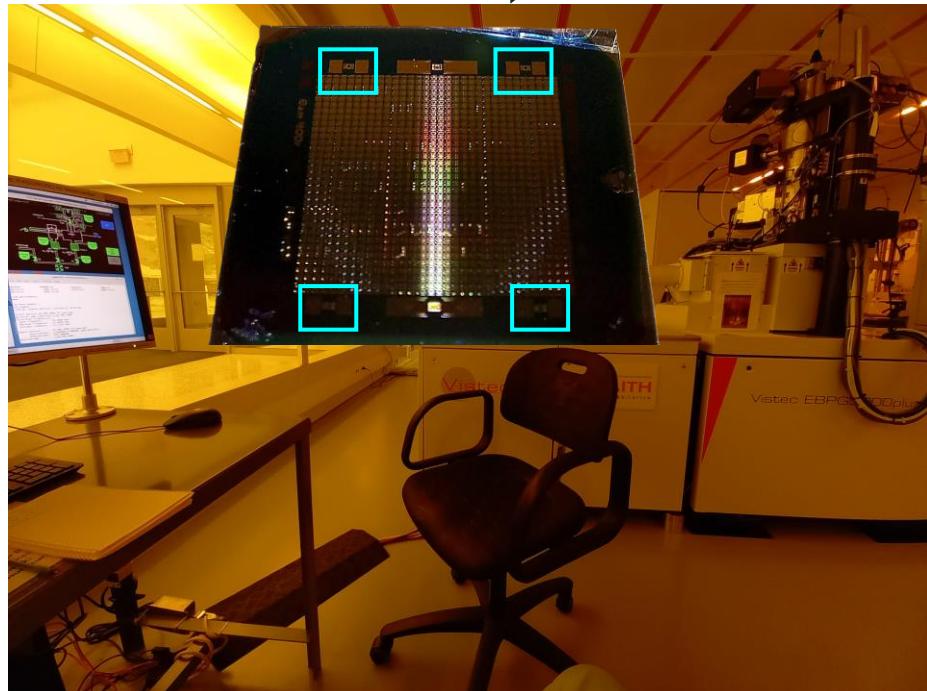
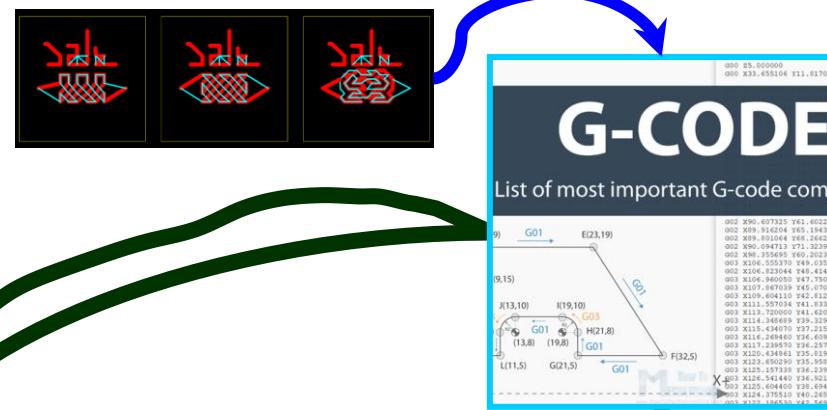
- CAD **DWG** → **DXF** → **GDS II** → Beamer → **GPF** → **CJOB** → **JOB File**



# E-Beam vs. 3D Printing vs. CNC Machining

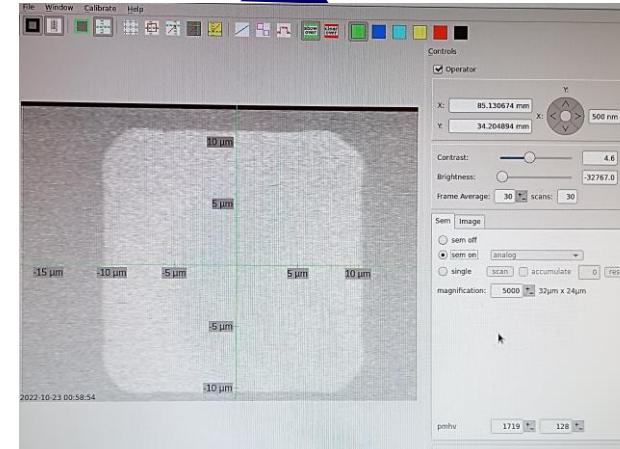
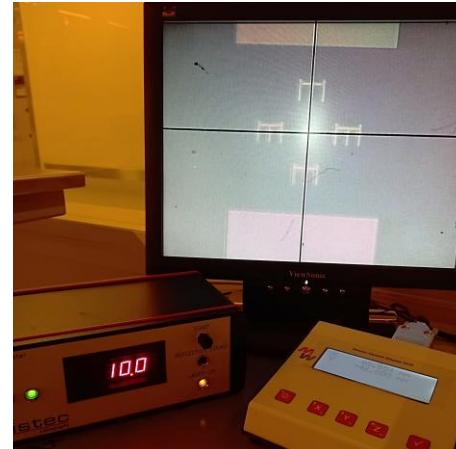
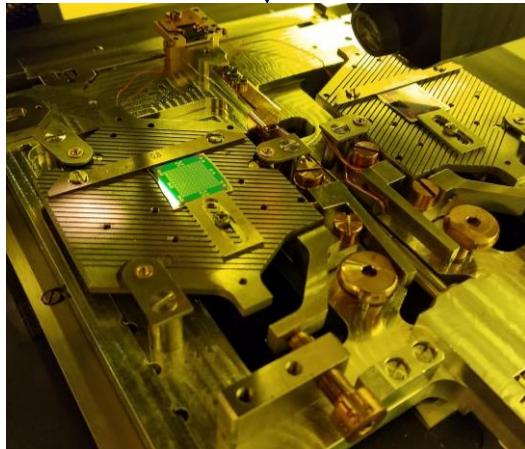
- Similarities:

- Uses of a type of **G-code** or coordinate system.
- Initial alignment procedure (reference points).
- CAD **DWG** → **DXF** → “the G-Code”.



# Maskless Direct Writing

- Doses:
  - For relatively larger features (**pads & stripes**):  $450 \mu\text{C}/\text{cm}^2$ .
  - For smaller features (**pillars**):  $825-875 \mu\text{C}/\text{cm}^2$ .
- Basically:
  - Rough Alignment → SEM-Aided Marker Location → Record Final Marker Position → & Write!



ce benal017  
cd jobs

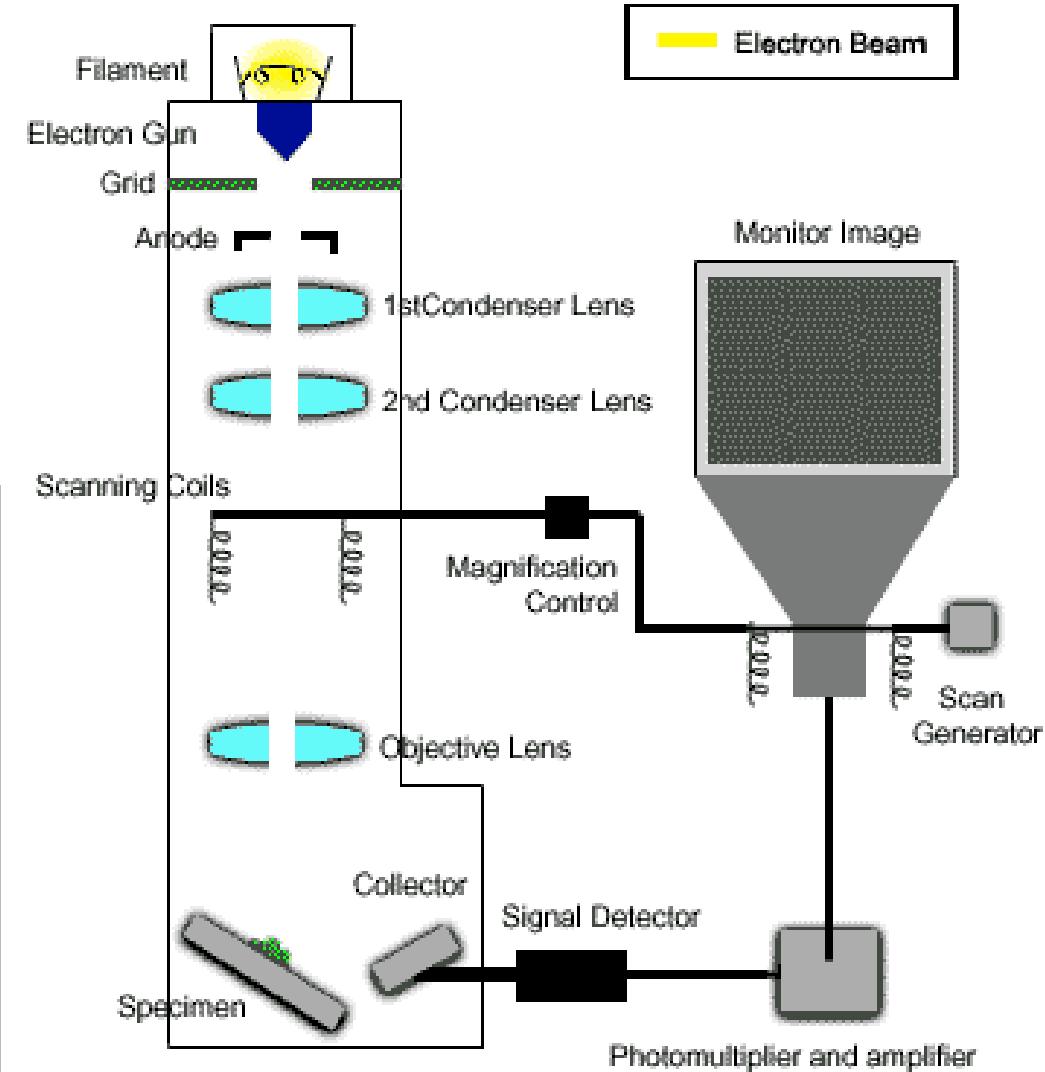
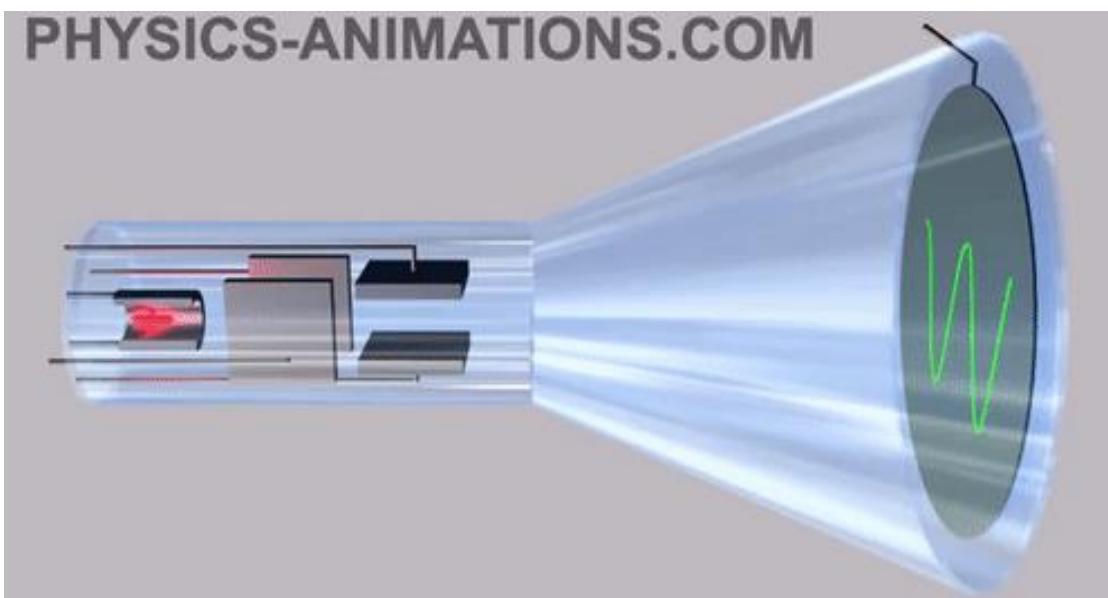
```
subl 1
pg select holder 3
mvm
beamload lna_300um_table.beam_100

pg move position 0,-500 --rel
mea_c;pg move position 55686,-46836 --rel
findmark rp20
mea_c;pg move position 55686,-32841 --rel
findmark rp20
mea_c;pg move position 68717,-46819 --rel
findmark rp20
mea_c;pg move position 68718,-32836 --rel
findmark rp20

job Superconducting_pMTJ_pillars.job 3 0 72
```

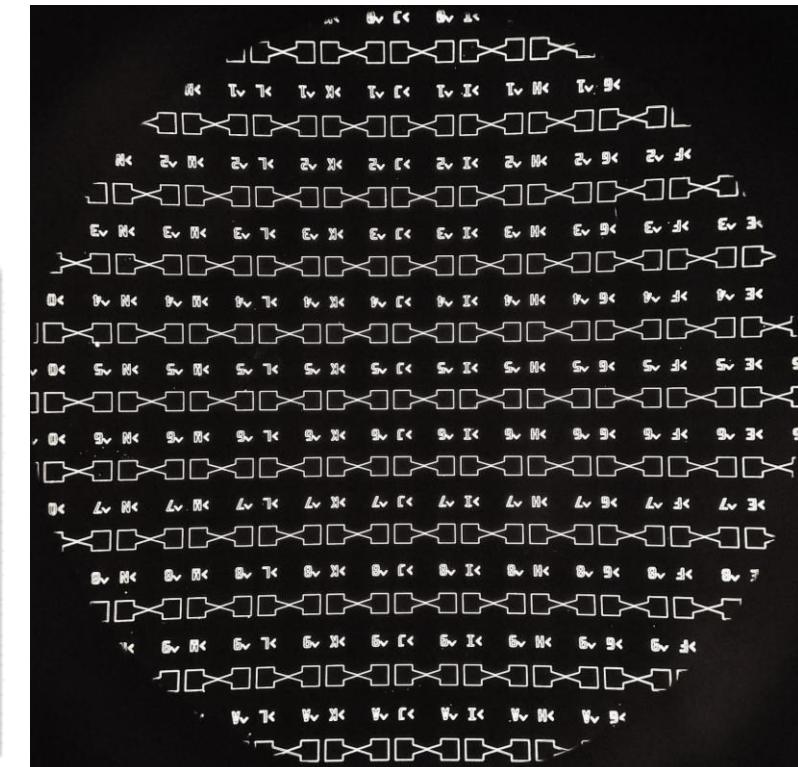
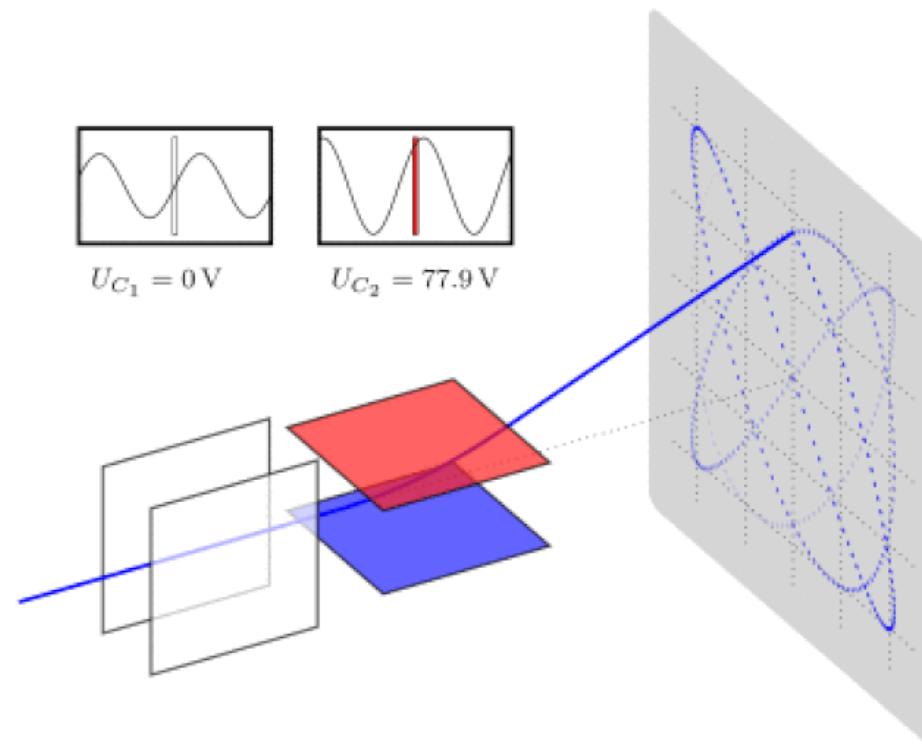
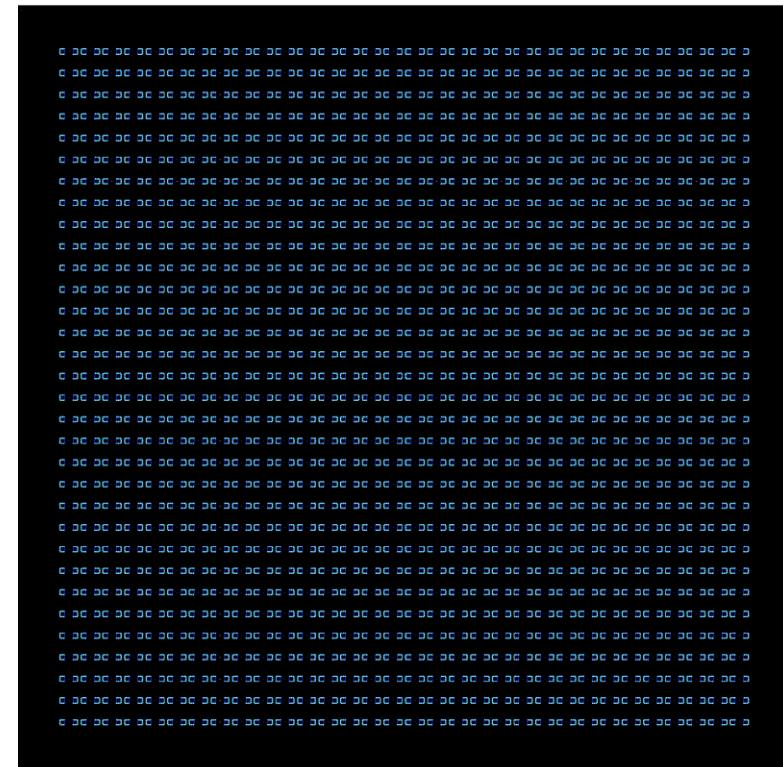
Confirm  
&  
Write!

# Bonus: Basic Operating Principle of Electron-Beam-Based Technology



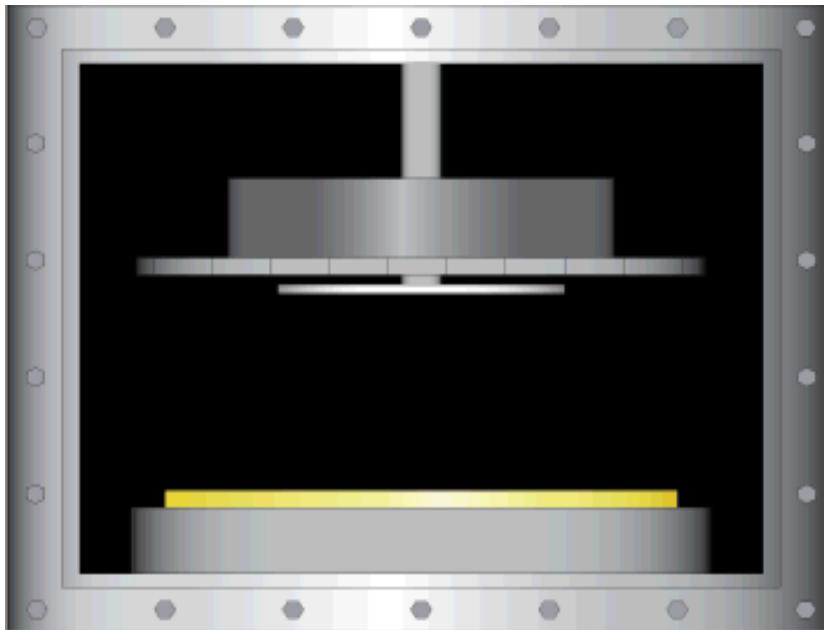
1. Taken from: *Wikimedia Commons*
2. Taken from: [makeagif.com](http://makeagif.com)

# Basic Operating Principle of Electron-Beam Exposed Features

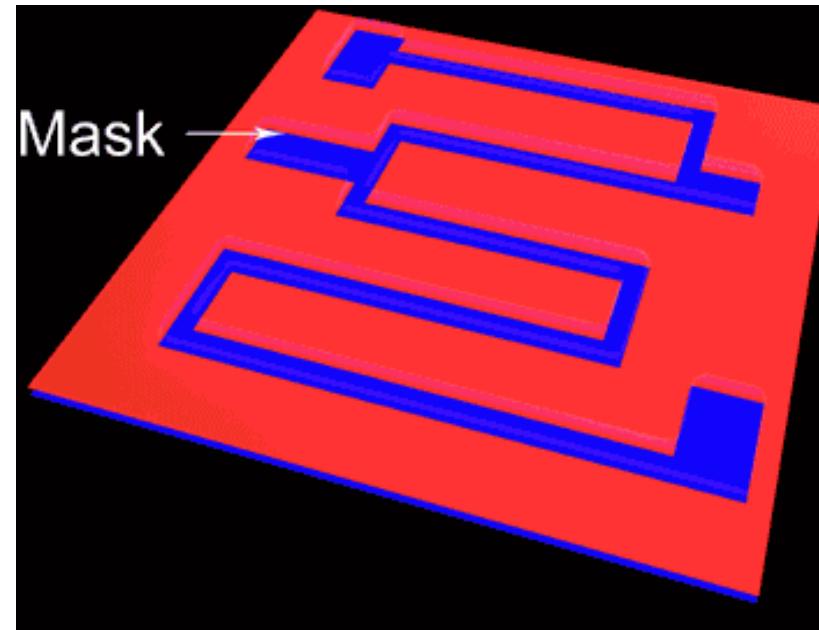


1. Taken from: Wikimedia commons

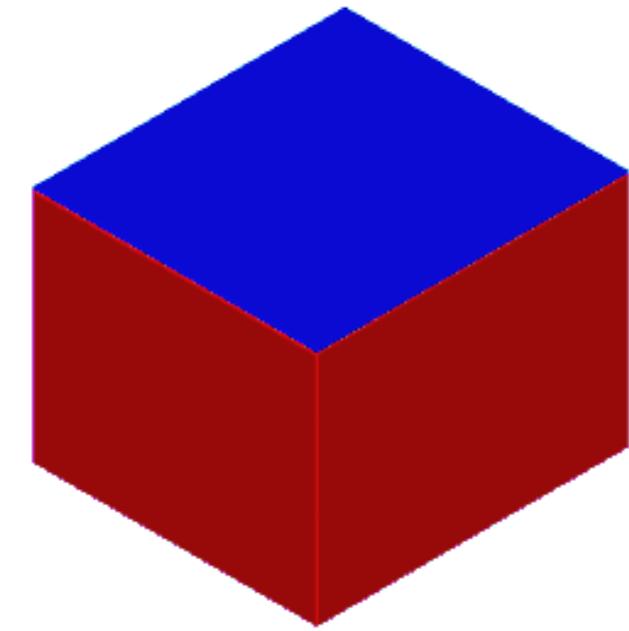
# Material Deposition & Etching



For depositing or growing materials

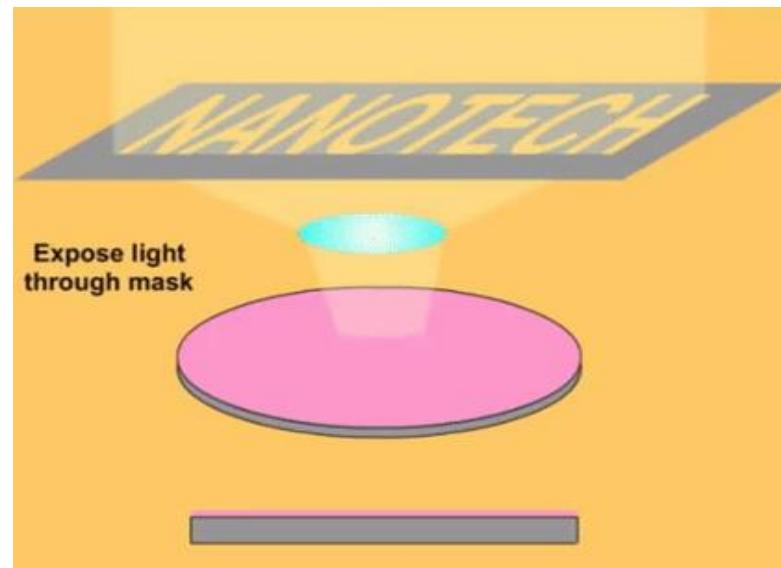


For removing or etching materials



Result

# 3 Examples of Lithography Systems

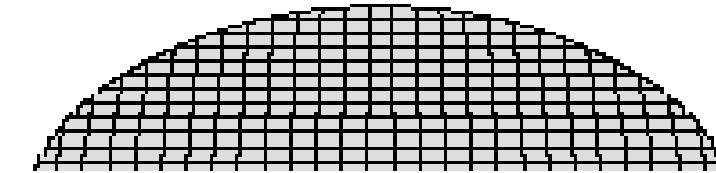


**Ultraviolet Lithography**

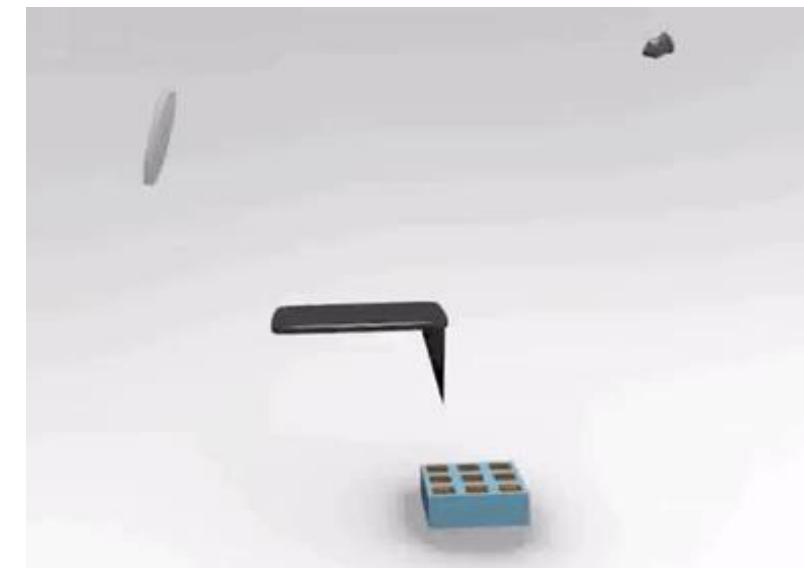
Vacuum Environment

Electron Gun

Wafer



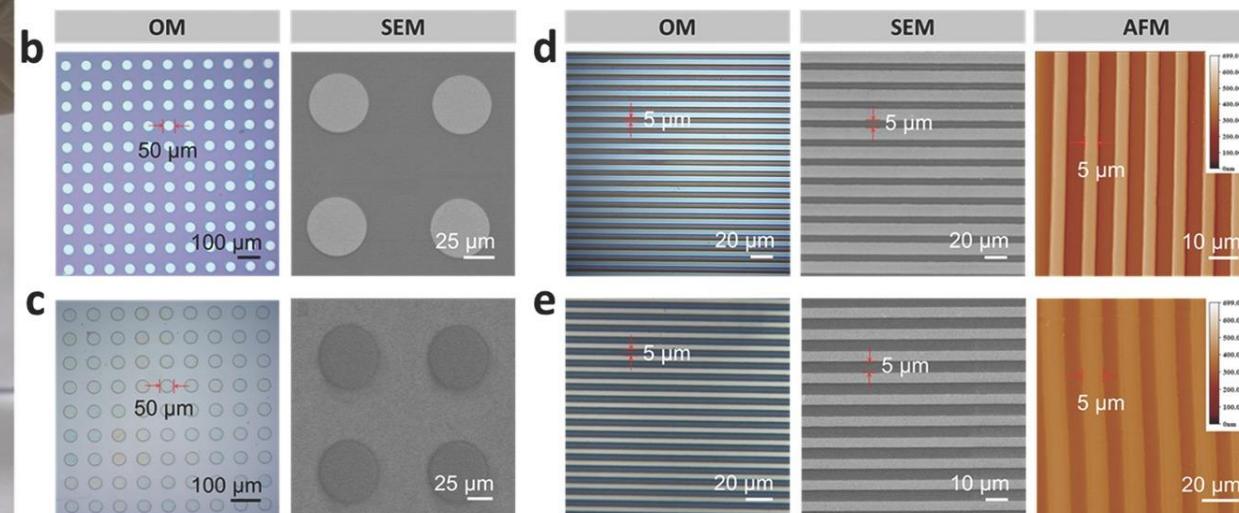
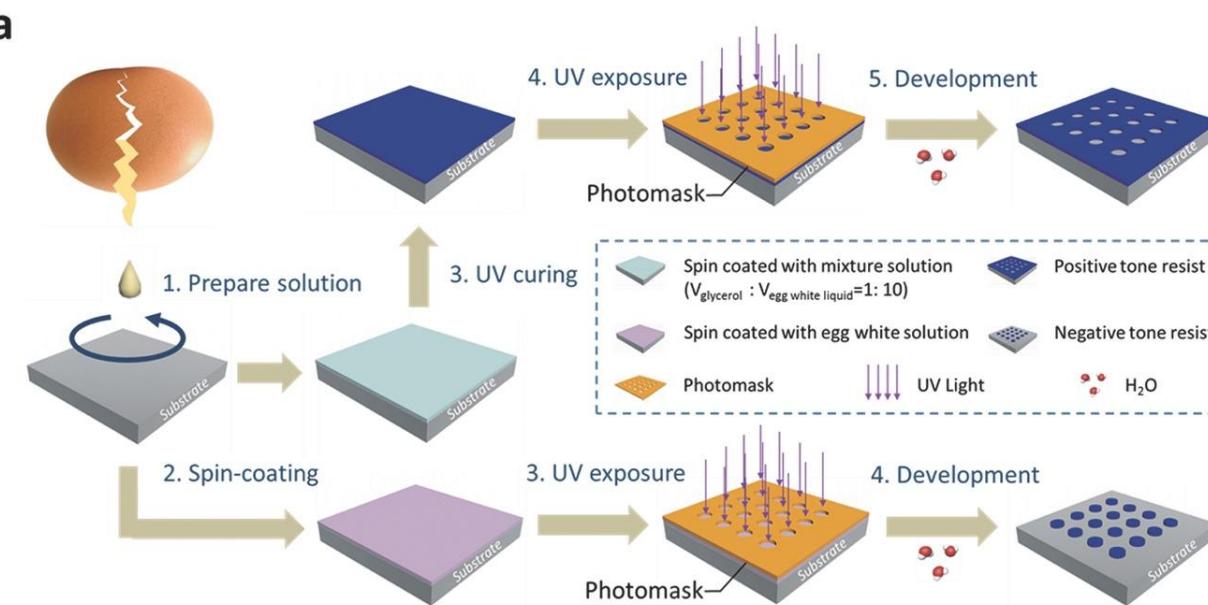
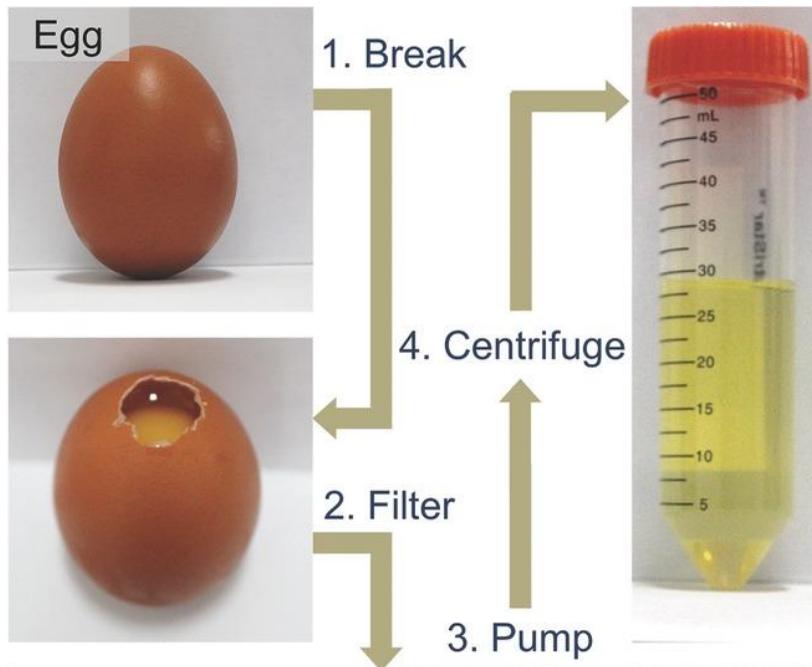
**Electron Beam Lithography**



**Scanning Probe Lithography**

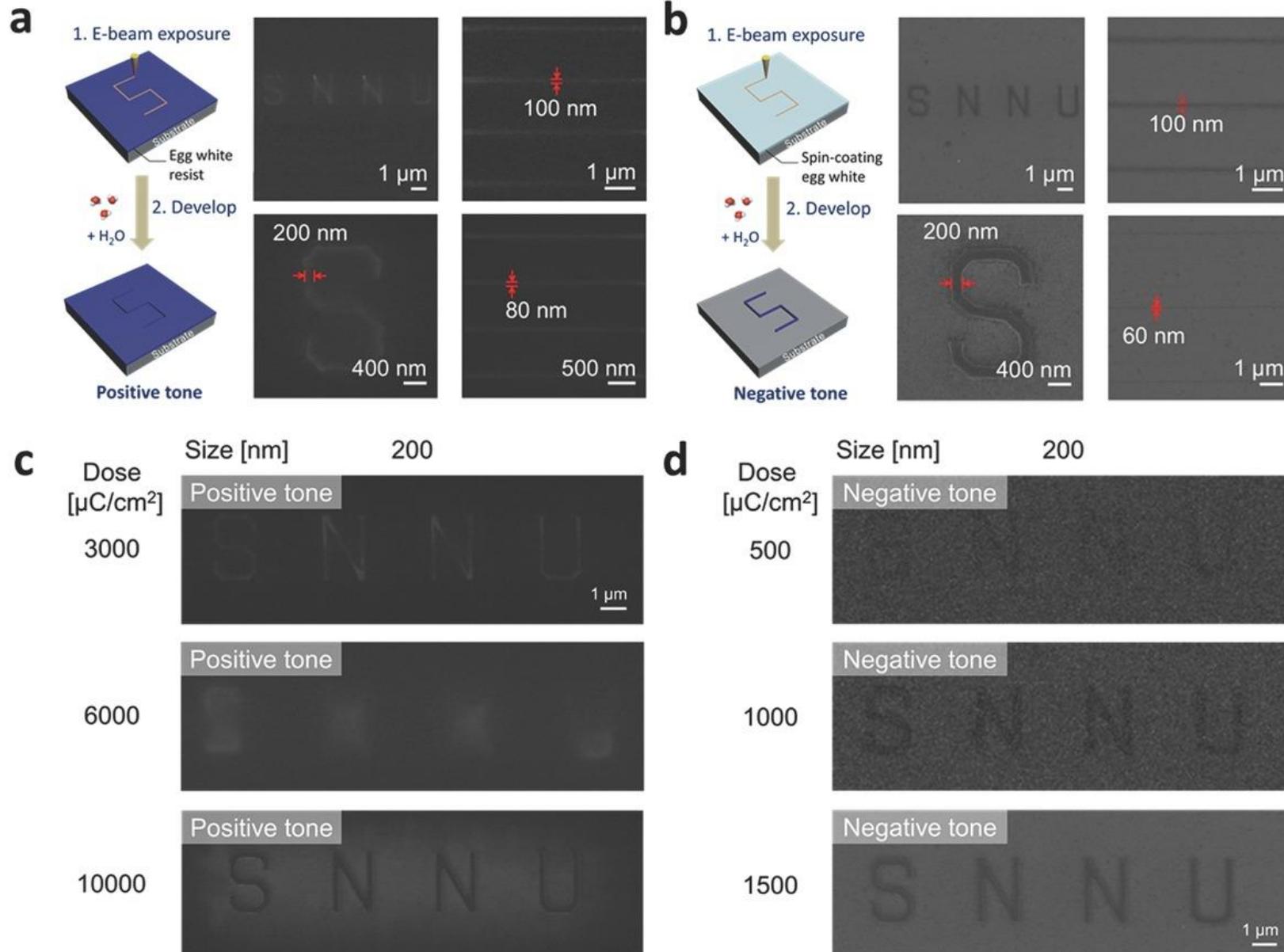
1. Taken from: [thumbs.gfycat.com](http://thumbs.gfycat.com)
2. Taken from: [wikipedia.org](https://en.wikipedia.org)
3. Taken from: [web.cecs.pdx.edu](http://web.cecs.pdx.edu)

# Green Lithography Methods

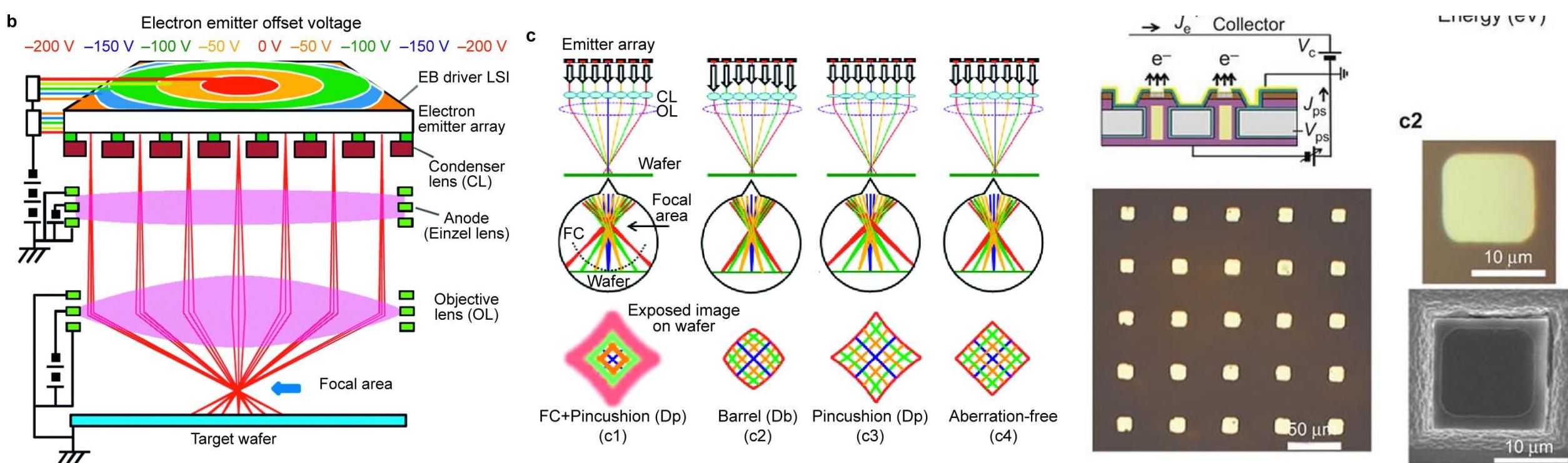


1. Jiang et al., *Advanced Materials Interfaces* (2022)

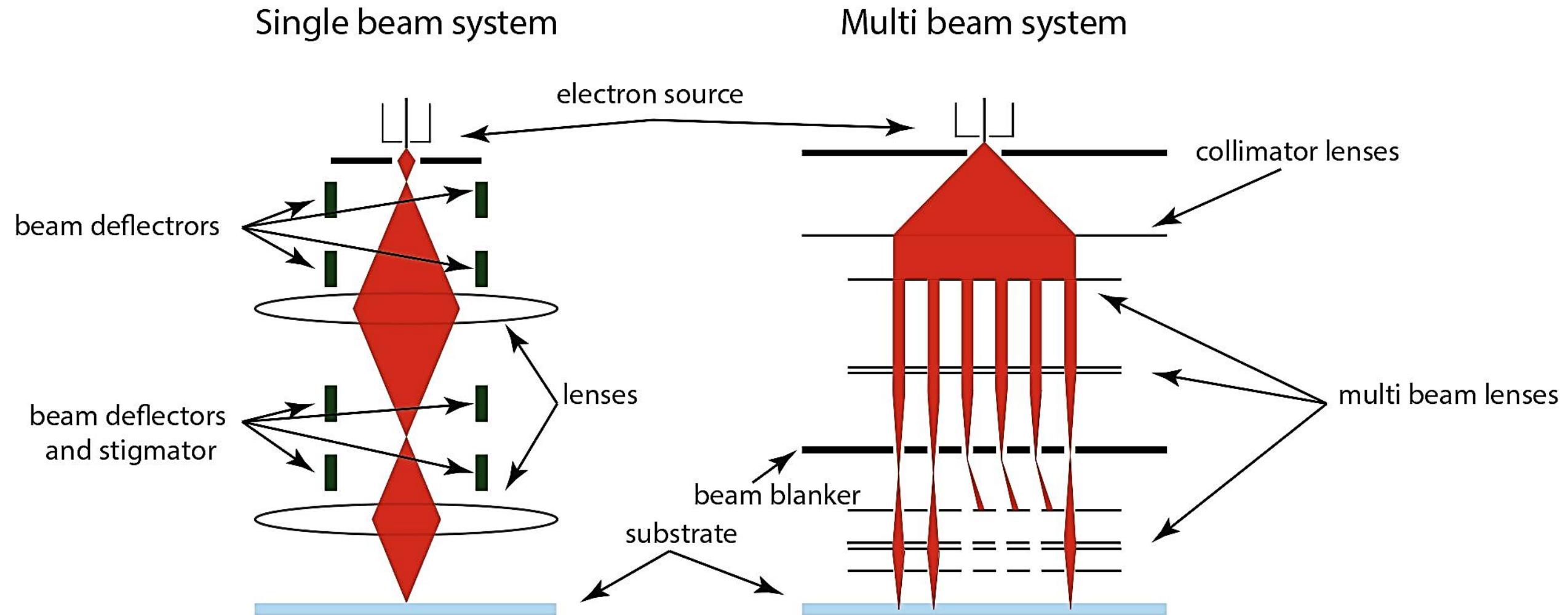
# Green Lithography Methods



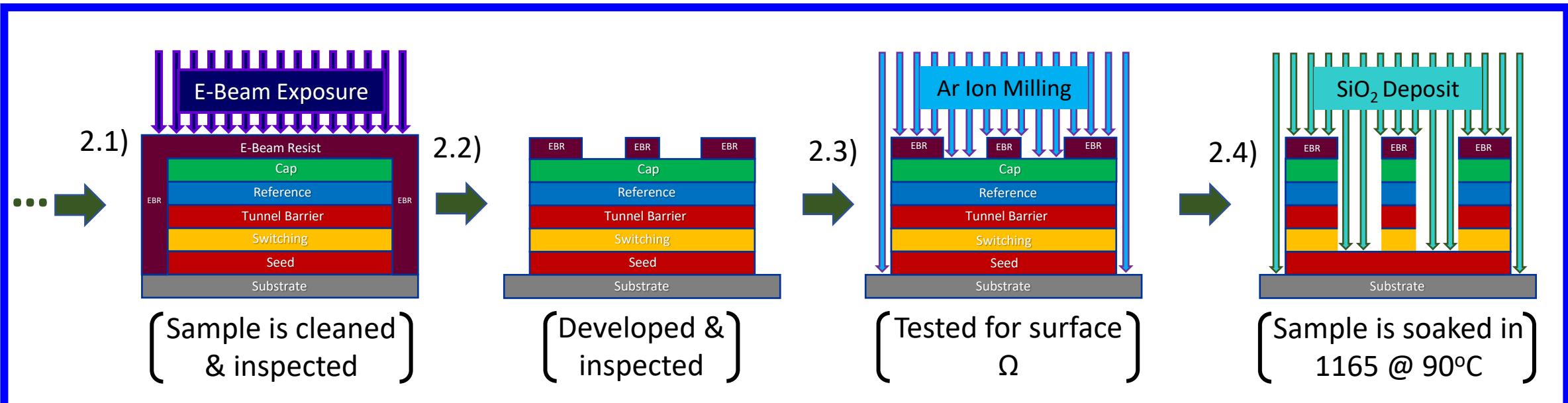
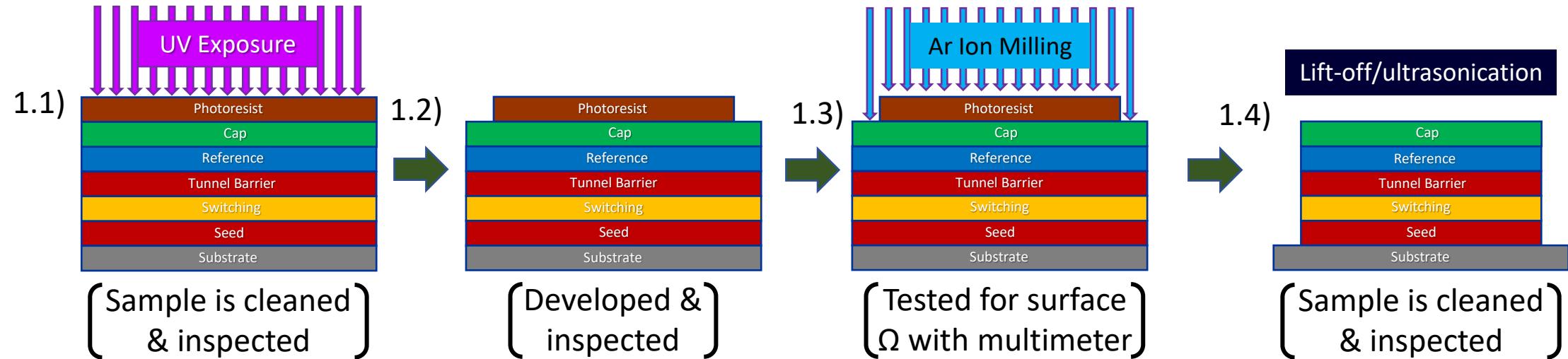
# Multi-Beam Direct-Writing



# Multi-Beam Direct-Writing



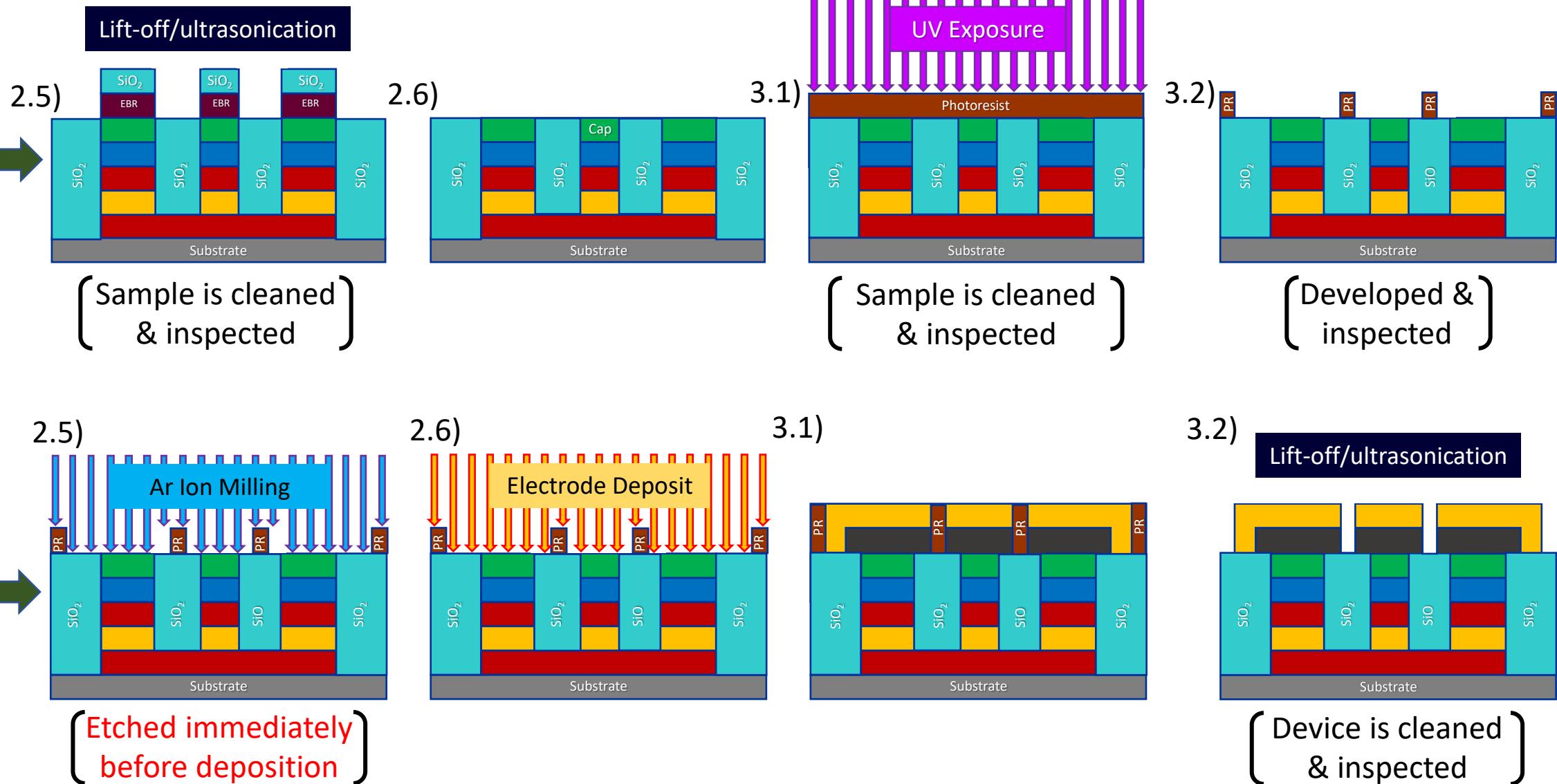
# Generic Example of Standard Fabrication Flow



\*PR = Photoresist    \*\*\*EBR = Electron-Beam Resist

\*\*  $\Omega$  = Resistance

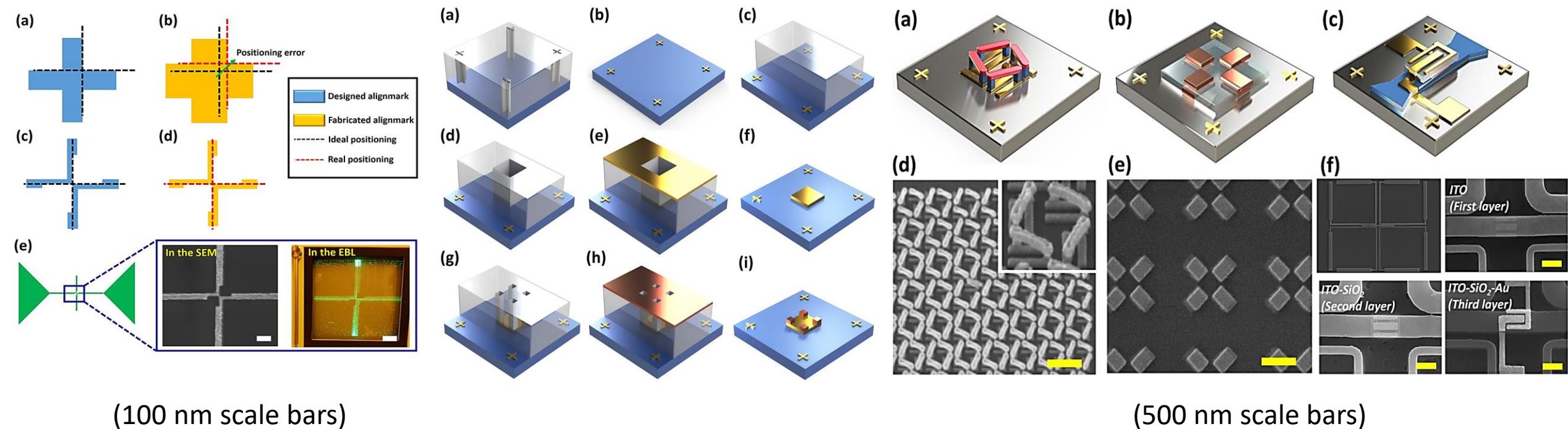
# Randomized Example of Standard Fabrication Flow



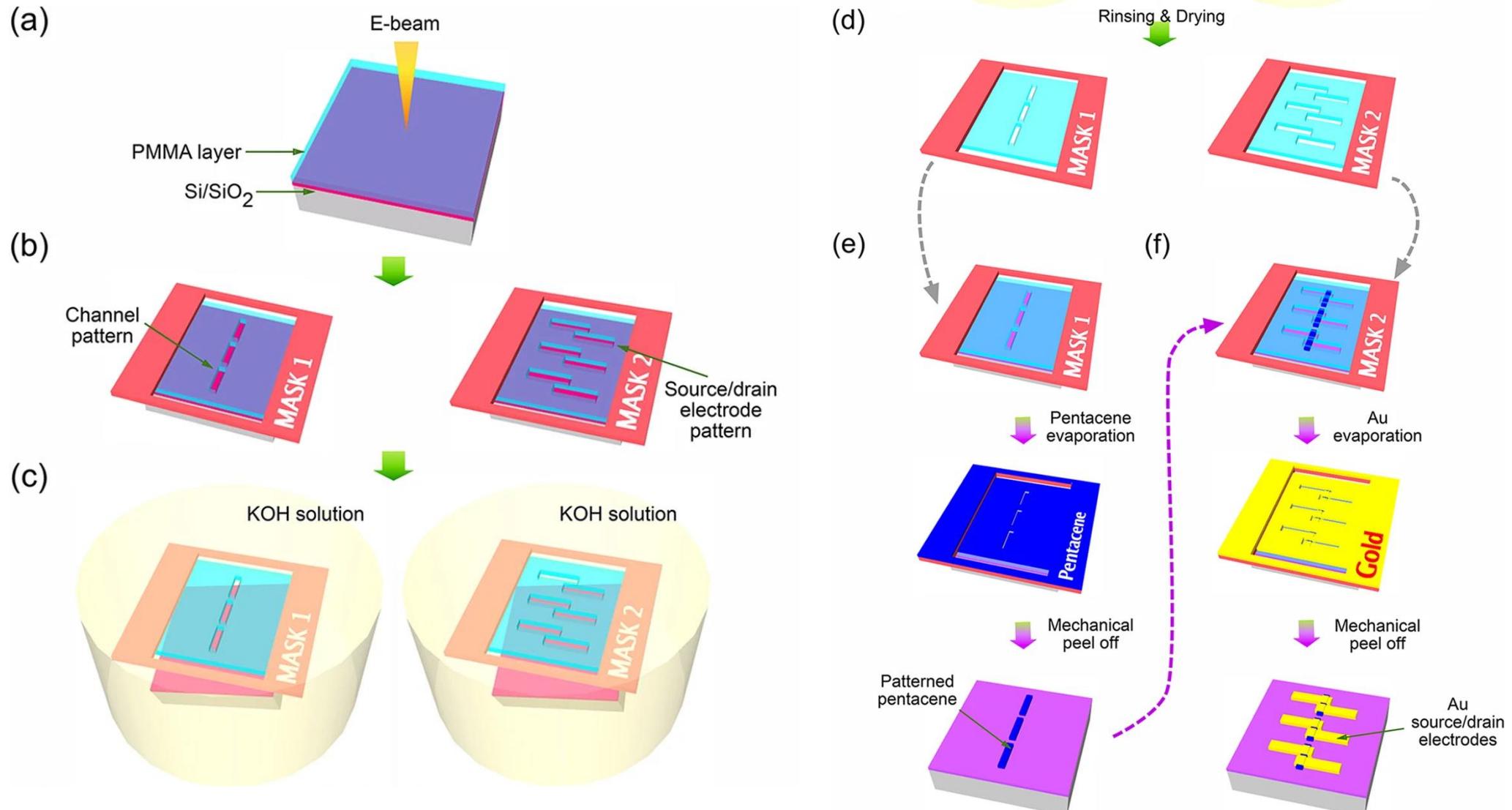
\*PR = Photoresist   \*\*EBR = Electron-Beam Resist  
\*\* Ω = Resistance



# Example of Overlay Nanostructures Fabricated with E-Beam

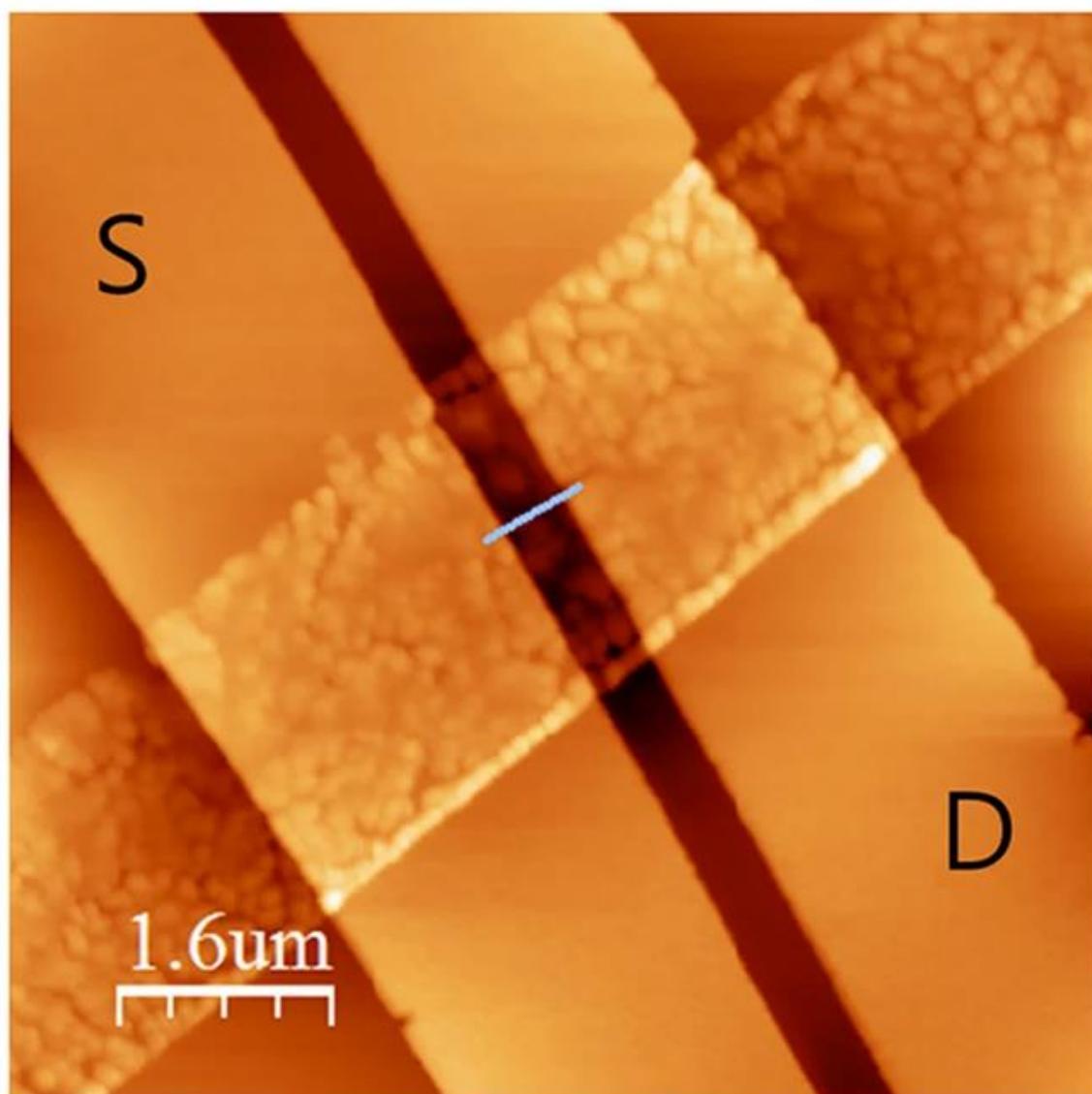


# Shadow Lithography for Nanowires

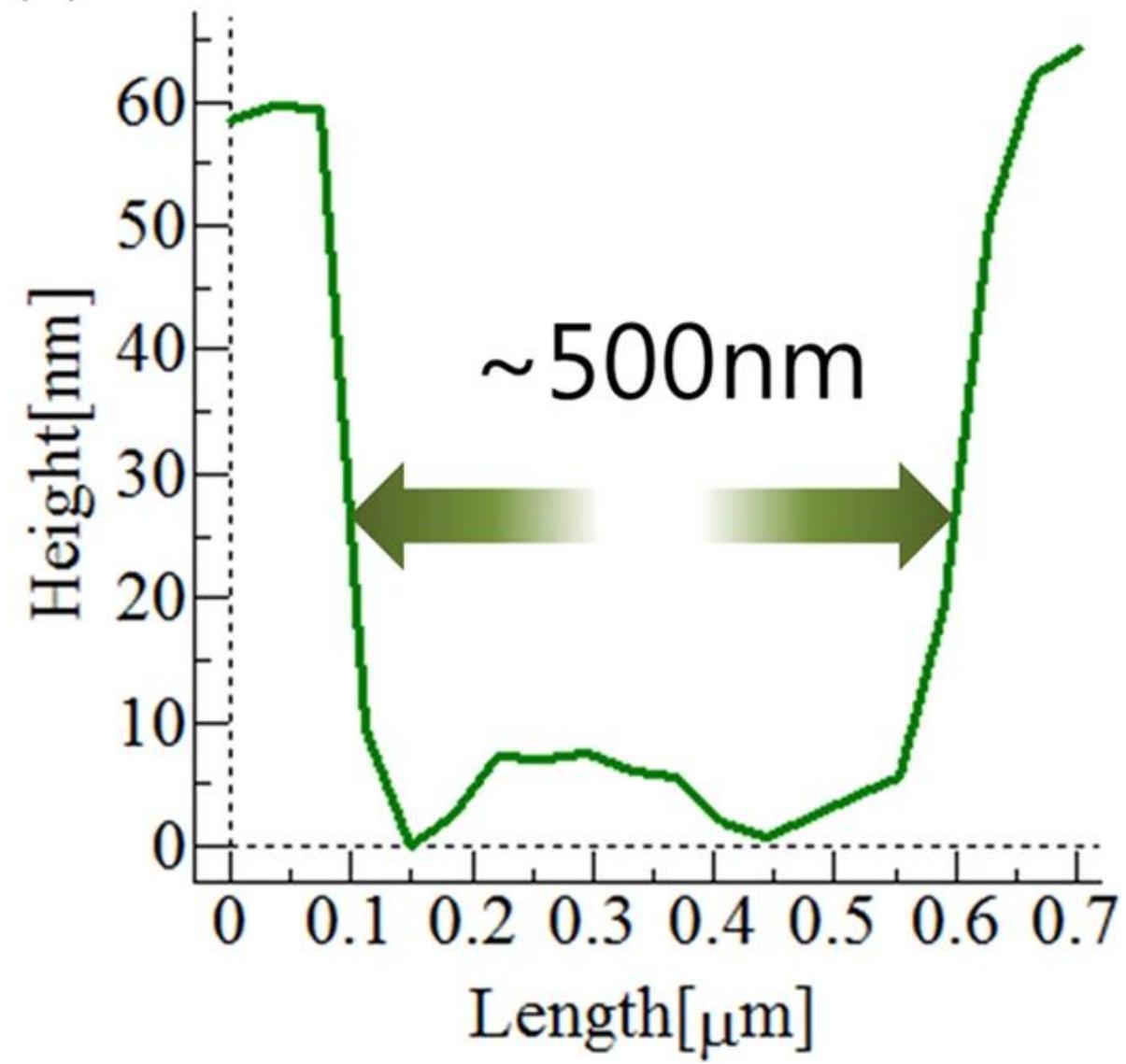


# Shadow Lithography for Nanowires

(a)

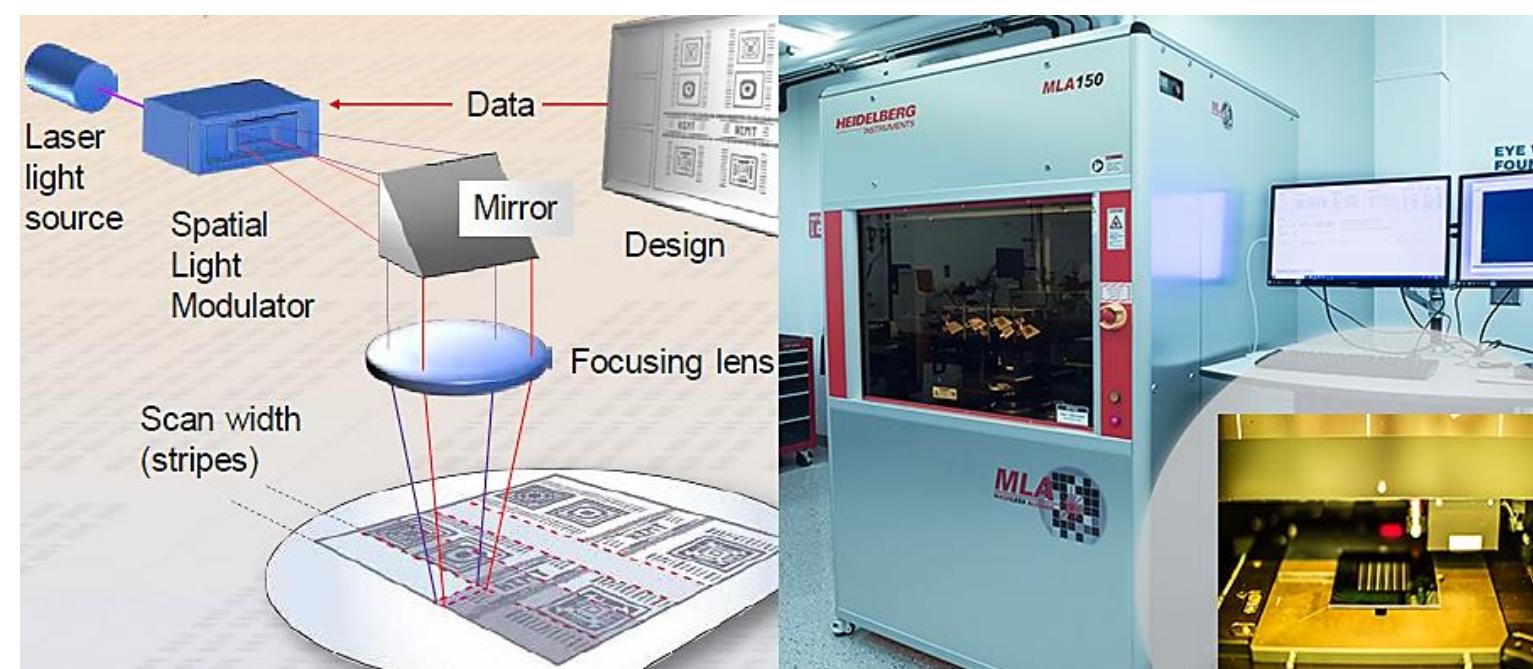
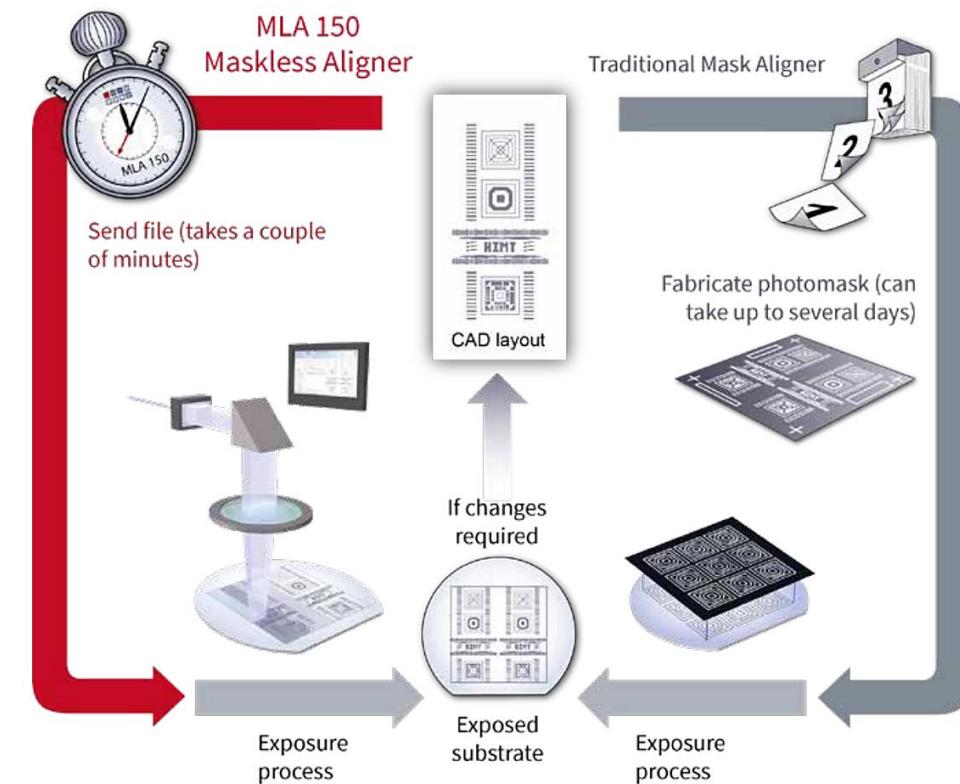


(b)



# Heidelberg MLA 150 Maskless Aligner

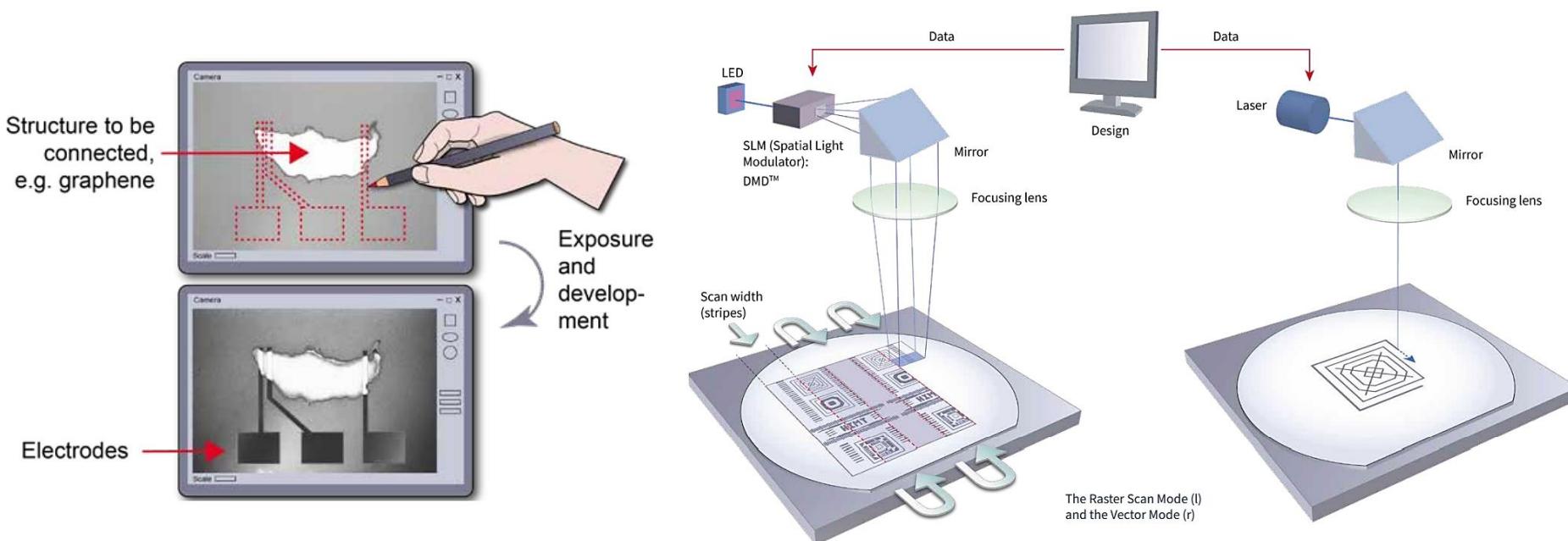
- LASER wavelength = 375 - 405 nm
- $50 \text{ mm} \times 50 \text{ mm}^2 = 4 \text{ min of writing time, } 0.6 \text{ micron}$
- Large machine
- Compatible with all broadband UV photoresists



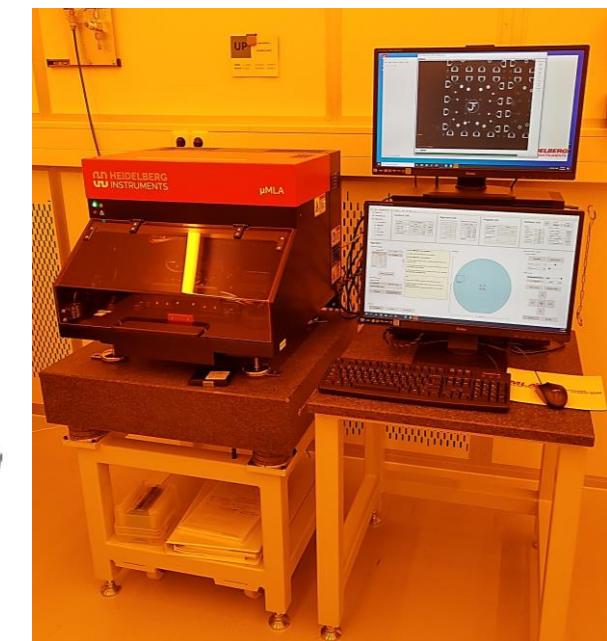
1. Heidelberg Instruments, *MLA150* (2021)

# Heidelberg μMLA Maskless Aligner

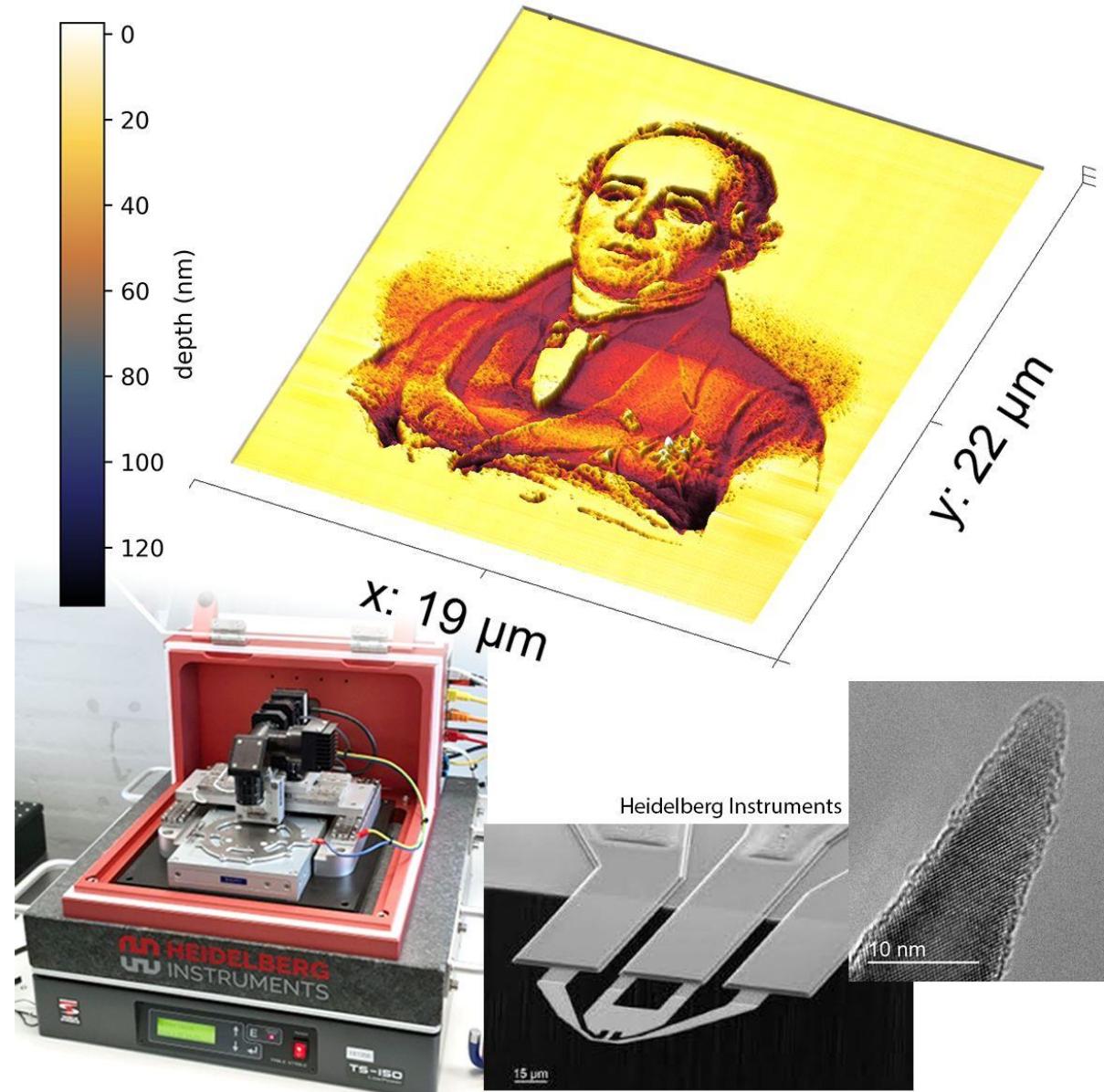
- LASER wavelength = 375 - 405 nm
- LED wavelength = 365 - 390 nm
- Smaller machine
- Compatible with all broadband UV photoresists



1. Heidelberg Instruments, μMLA (2021)

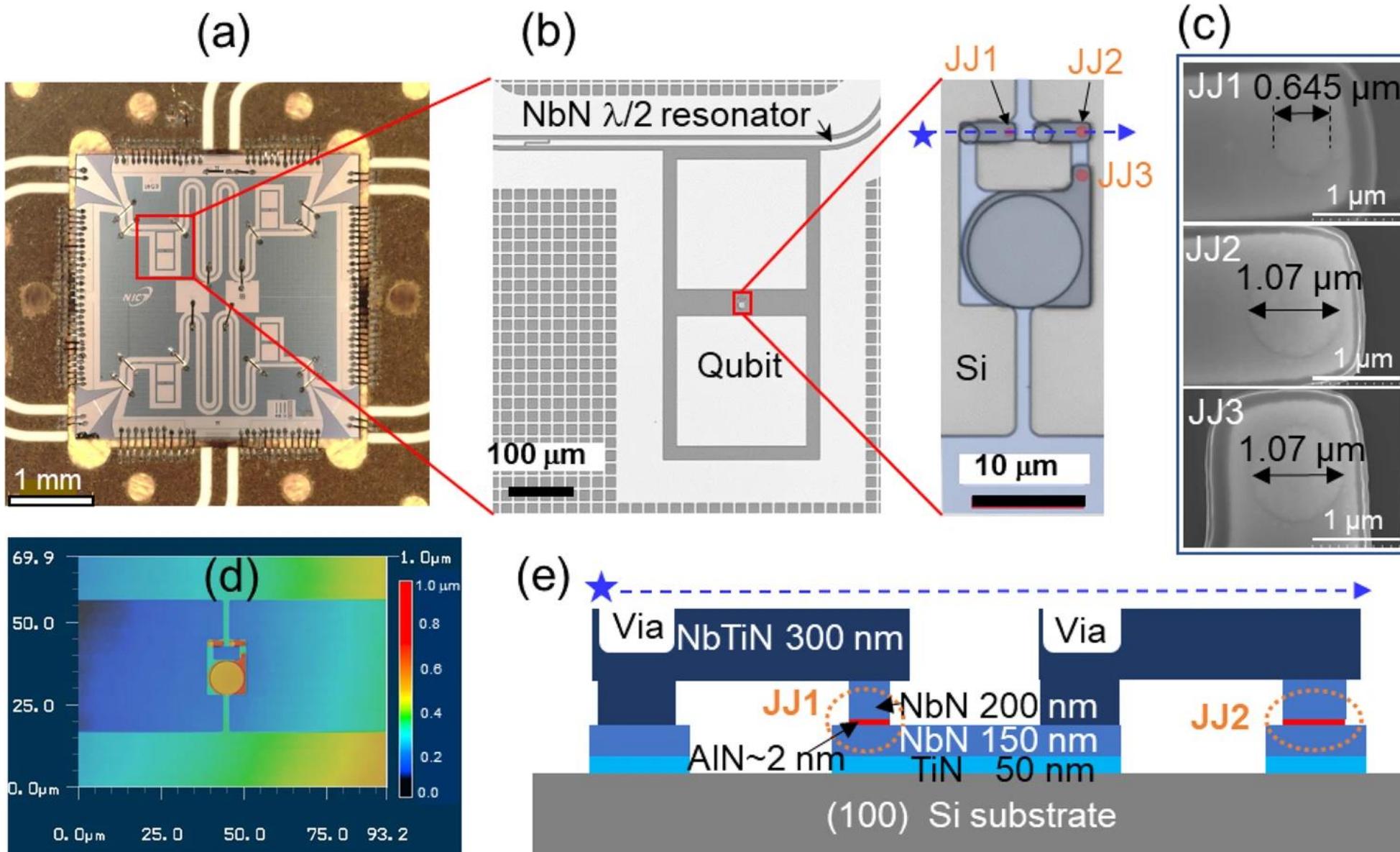


# Scanning Thermal Probe Lithography for Custom Designs

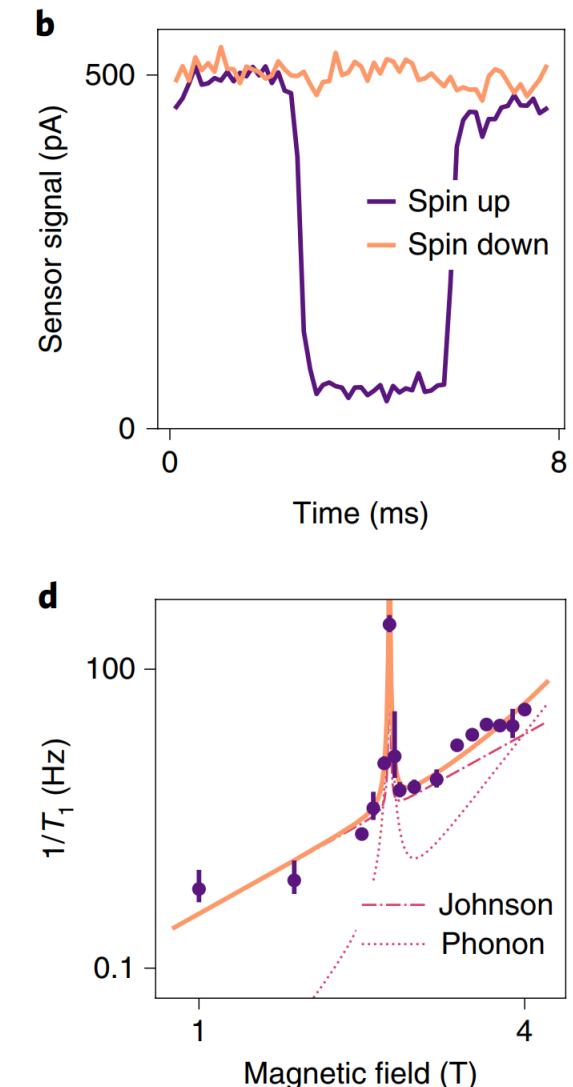
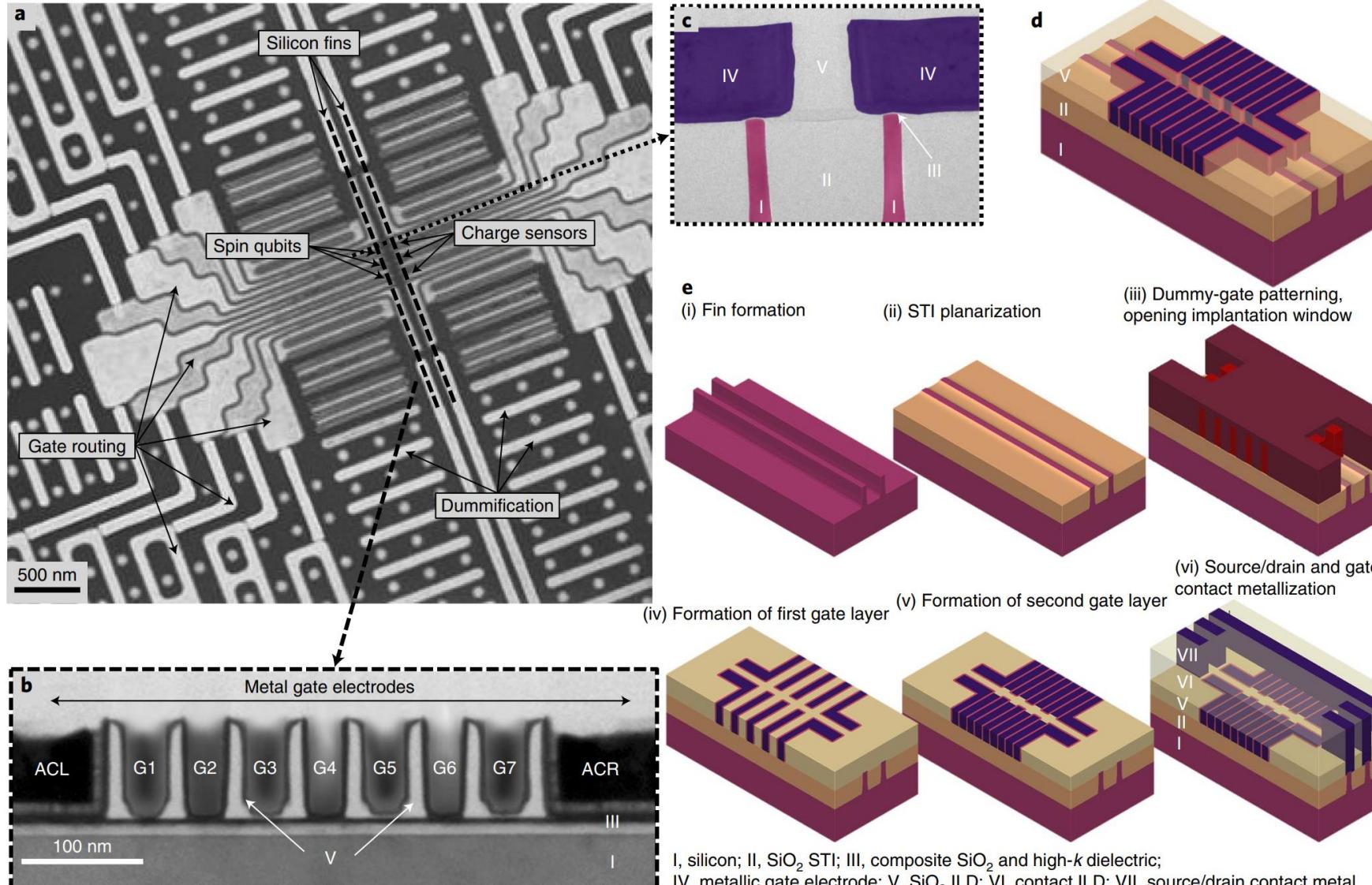


1. From: Technical University of Denmark-Physics & Heidelberg Instruments

# Superconducting All-Nitride Junctions



# Example of a Semiconductor Fab Spin Qubit



# Summary

- Electron beam writing is a great tool for **high-resolution nanopatterning**.
- The direct write operation allows for complex **design imports**.
- The machine setup can be compared with **CNC-based technologies**.
  - More or less.
- If trained on the equipment, **transferring skills** to other **maskless-based lithography** systems is a little easier.
- Always watch out for charge build-up!
- Next week we will talk about hardware control & imaging.